

### BDW23/A/B/C

# Hammer Drivers, Audio Amplifiers Applications

- Power Darlington TR
- Complement to BDW24, BDW24A, BDW24B and BDW24C respectively



1.Base 2.Collector 3.Emitter

### **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BDW23	45	V
	: BDW23A	60	V
	: BDW23B	80	V
	: BDW23C	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BDW23	45	V
	: BDW23A	60	V
	: BDW23B	80	V
	: BDW23C	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	6	Α
I <sub>CP</sub>	*Collector Current (Pulse)	8	Α
I <sub>B</sub>	Base Current	0.2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	50	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

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### Electrical Characteristics $\rm T_{C}{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit s
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage : BDW23 : BDW23A : BDW23B	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0	45 60 80			V V
	: BDW23B		100			V
Ісво	Collector Cut-off Current : BDW23 : BDW23A : BDW23B : BDW23C	$V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$			200 200 200 200	μΑ μΑ μΑ μΑ
I <sub>CEO</sub>	Collector Cut-off Current : BDW23 : BDW23A : BDW23B : BDW23C	$V_{CE} = 22V, I_B = 0$ $V_{CE} = 30V, I_B = 0$ $V_{CE} = 40V, I_B = 0$ $V_{CE} = 50V, I_B = 0$			500 500 500 500	μΑ μΑ μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			2	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 3V, I_{C} = 1A$ $V_{CE} = 3V, I_{C} = 2A$ $V_{CE} = 3V, I_{C} = 6A$	1000 750 100		20000	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 8mA$ $I_C = 6A, I_B = 60mA$			2 3	V V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 8mA$			2.5	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage	$V_{CE} = 3V, I_{C} = 1A$ $V_{CE} = 3V, I_{C} = 6A$			2.5 3	V V
$V_{F}$	* Parallel Diode Forward Voltage	I <sub>F</sub> = 2A			1.8	V

<sup>\*</sup> Pulse Test: PW =300μs, duty Cycle =1.5% Pulsed

# **Typical Characteristics**



Figure 1. DC current Gain

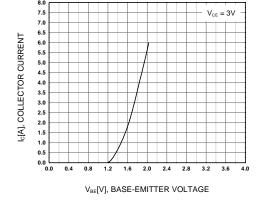


Figure 2. Collector-Emitter Saturation Voltage

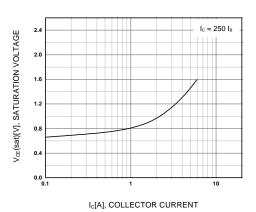


Figure 3. Base-Emitter On Voltage

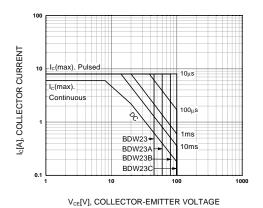


Figure 4. Safe Operating Area

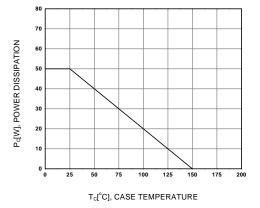
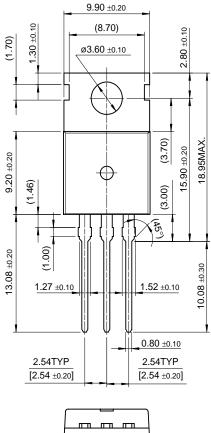


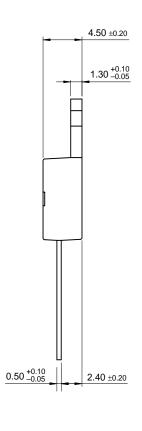
Figure 5. Power Derating

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# **Package Demensions**

### TO-220





10.00 ±0.20

Dimensions in Millimeters

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